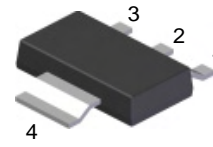


**Features**

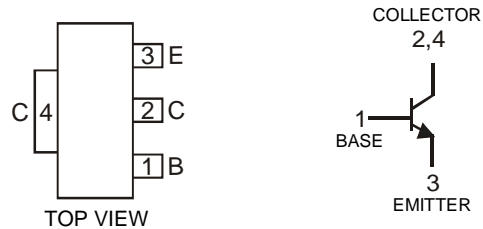
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DZT5401)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 3)**



SOT-223

**Mechanical Data**

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish - Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.112 grams (approximate)



Schematic and Pin Configuration

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	160	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	I <sub>C</sub>	600	mA

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation @T <sub>A</sub> = 25°C (Note 3)	P <sub>D</sub>	1	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 3)	R <sub>θJA</sub>	125	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 4)</b>					
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	180	—	V	I <sub>C</sub> = 100μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	160	—	V	I <sub>C</sub> = 1.0mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6.0	—	V	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CBO</sub>	—	50	nA	V <sub>CB</sub> = 120V, I <sub>E</sub> = 0
Emitter Cutoff Current	I <sub>EBO</sub>	—	50	nA	V <sub>CB</sub> = 120V, I <sub>E</sub> = 0, T <sub>A</sub> = 100°C
<b>ON CHARACTERISTICS (Note 4)</b>					
DC Current Gain	h <sub>FE</sub>	80	—	—	I <sub>C</sub> = 1.0mA, V <sub>CE</sub> = 5.0V
		80	250	—	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 5.0V
		30	—	—	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 5.0V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	0.15	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA
		—	0.20	V	I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	—	1.0	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA
		—	—	V	I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	C <sub>obo</sub>	—	6.0	pF	V <sub>CB</sub> = 10V, f = 1.0MHz, I <sub>E</sub> = 0
Small Signal Current Gain	h <sub>fe</sub>	50	200	—	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f <sub>T</sub>	100	300	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 10mA, f = 100MHz
Noise Figure	NF	—	8.0	dB	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 200μA, R <sub>S</sub> = 1.0kΩ, f = 1.0kHz

- Notes:
1. No purposefully added lead.
  2. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  3. Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤ 2%.

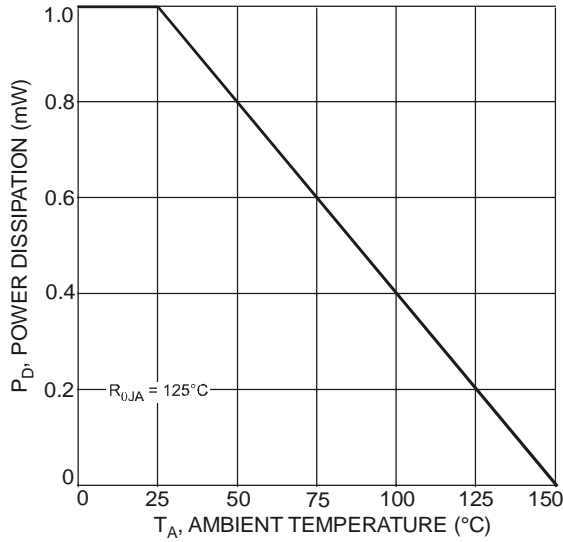


Fig. 1 Max Power Dissipation vs. Ambient Temperature

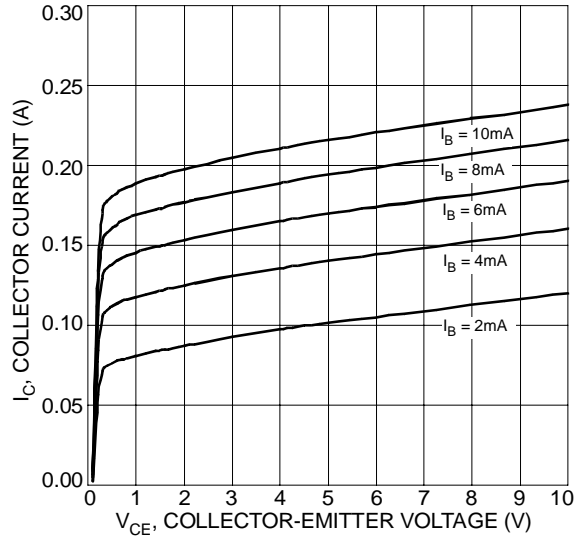


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

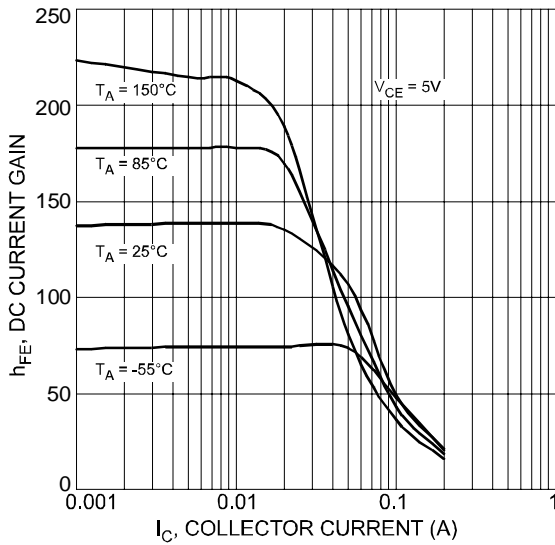


Fig. 3 Typical DC Current Gain vs. Collector Current

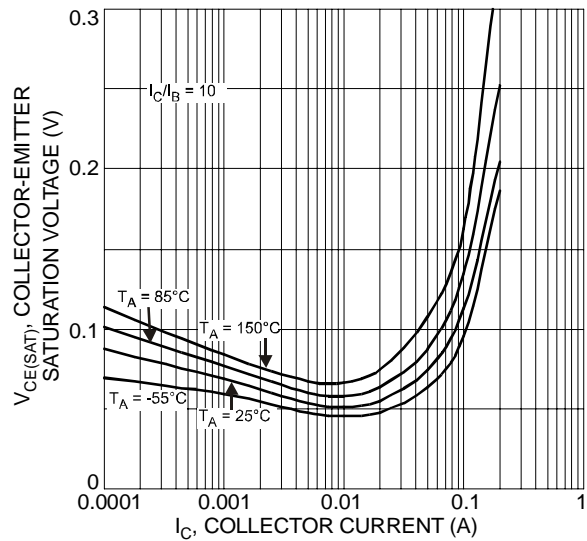


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

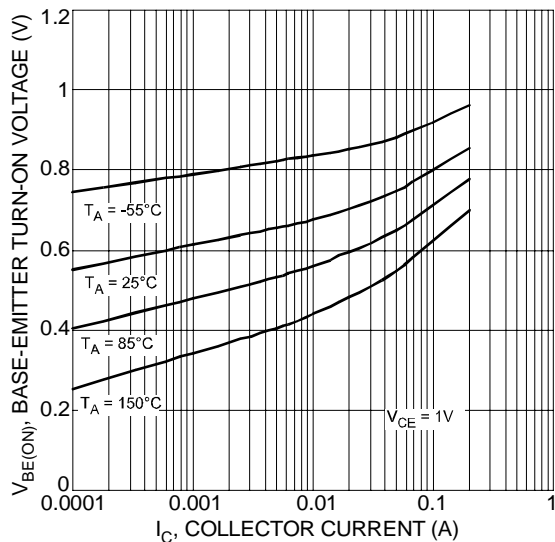


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

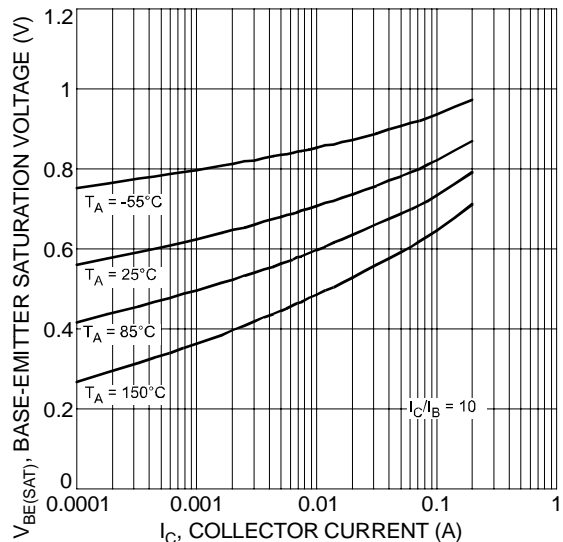


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

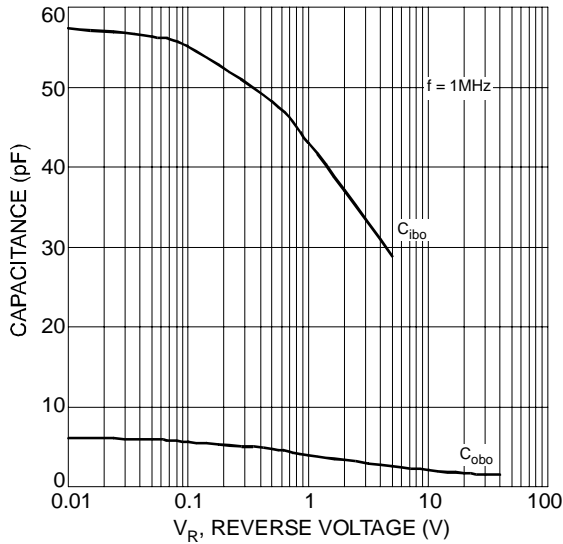


Fig. 7 Typical Capacitance Characteristics

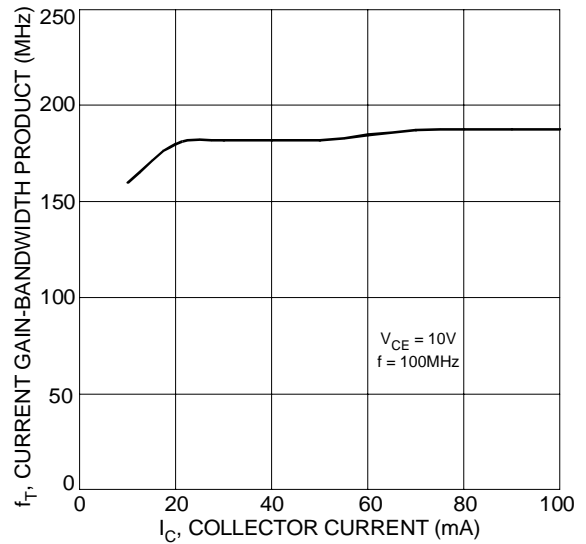


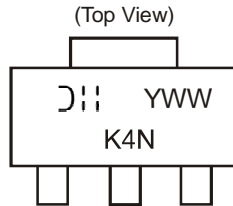
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

## Ordering Information (Note 5)

Device	Packaging	Shipping
DZT5551-13	SOT-223	2500/Tape & Reel

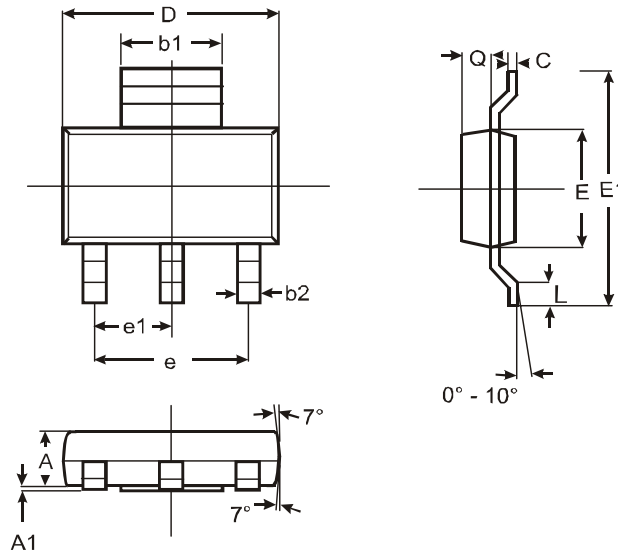
Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

## Marking Information



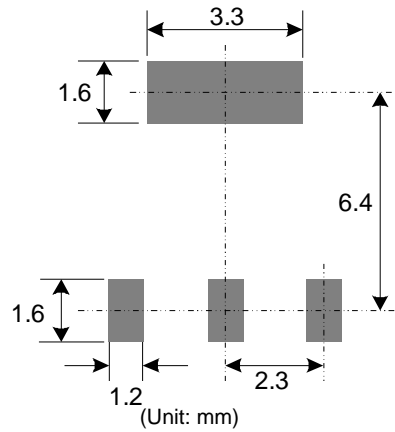
K4N = Product type marking code  
 DZT = Manufacturer's code marking  
 YWW = Date code marking  
 Y = Last digit of year ex: 7 = 2007  
 WW = Week code 01 - 52

## Package Outline Dimensions



SOT-223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b1	2.90	3.10	3.00
b2	0.60	0.80	0.70
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	—	—	4.60
e1	—	—	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

## Suggested Pad Layout



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